

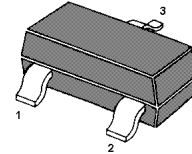
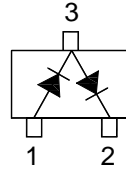
1SS396

Silicon Epitaxial Schottky Barrier Diode

for low voltage high speed switching application

Features

- Low forward voltage
- Low reverse current



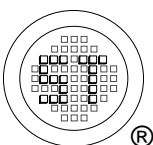
Marking Code: **T9**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current ($t = 10\text{ ms}$)	I_{FSM}	1	A
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

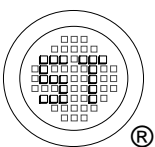
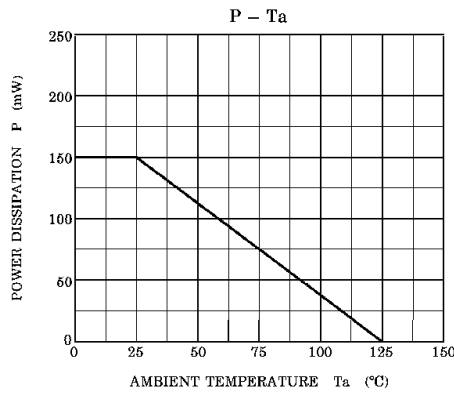
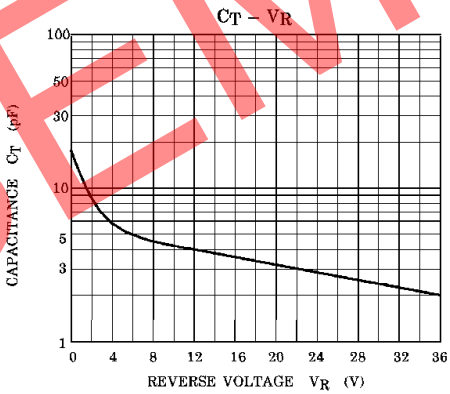
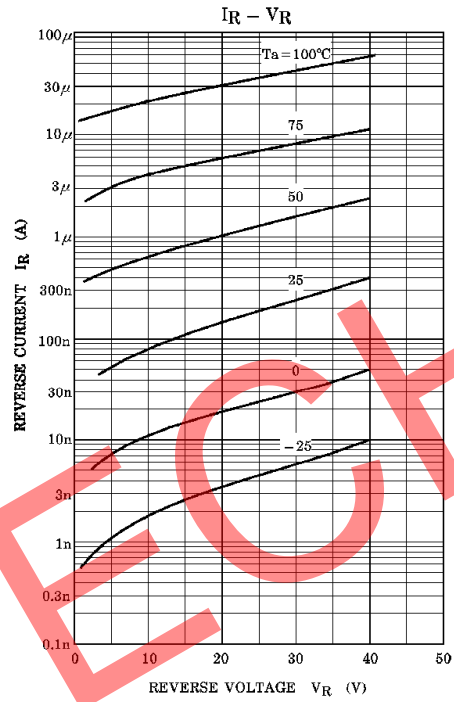
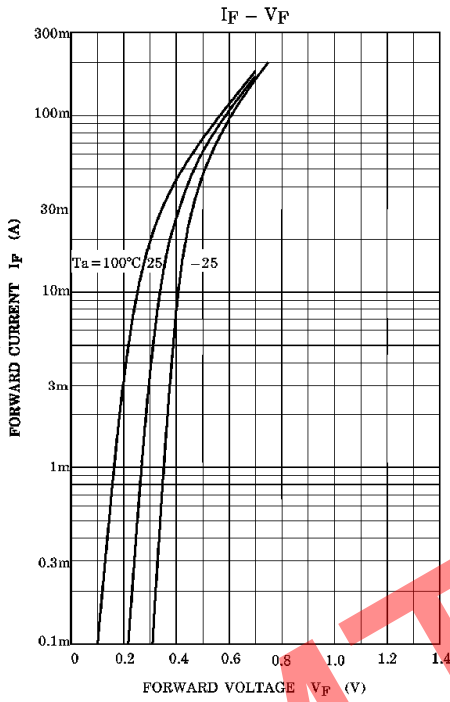
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	-	0.6	V
Reverse Current at $V_R = 40\text{ V}$	I_R	-	5	μA
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	45	-	V
Total Capacitance at $V_R = 0, f = 1\text{ MHz}$	C_{tot}	-	25	pF



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